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L8: (2313) MQW
L9: (12607) 7 8
L10: (536) 9 and 6
L11: (7) 10 and 2
L12: (76) multilayer adj quantum adj well
L13: (10) 12 and nitride
L14: (9) 13 and barrier
L15: (67) p-type adj barrier adj layer
L16: (66) n-type adj barrier adj layer
L17: (27) 15 and 16
L18: (12) 17 and nitride
Failed

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DBs   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   ☐ Plurals
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17 and nitride

BRS form   IS&R   Image   Text   HTML

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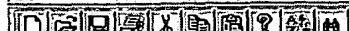
L2: (175) n-type adj nitride
L3: (5) 2 and bragg
L4: (0) active adj region adj with$1 adj indium
L5: (27053) active adj region
L6: (1882) 5 and indium
L7: (12035) quantum adj well
L8: (2313) MQW
L9: (12607) 7 8
L10: (536) 9 and 6
L11: (7) 10 and 2
Failed
(27) (((semiconductor and gate) and isotropic) and (n

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10 and 2

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- Drafts
  - BRS: semiconductor and diode
  - BRS: reference adj voltage adj identification
  - BRS: programmable adj logic
- Pending
- Active
  - L1: (14) n-type adj bragg adj reflector
  - L2: (175) n-type adj nitride
  - L3: (5) 2 and bragg
- Failed
  - (27) (((semiconductor and gate) and isotropic) and (n
  - (213) (((semiconductor and gate) and isotropic) and (

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2 and bragg

BRS form   IS&R   Image   Text   HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	☐	☐	US 20020056846 A1	20020516	22	Nitride semiconductor light emitting device and apparatus including the sa	257/86	257/87	
2	☐	☐	US 20020054617 A1	20020509	25	Nitride semiconductor laser device and optical device using the same	372/46	372/45	
3	☐	☐	US 20010035532 A1	20011101	16	Nitride semiconductor laser device and optical pickup apparatus therewit	257/103		
4	☐	☐	US 6242761 B1	20010605	19	Nitride compound semiconductor light emitting device	257/94	257/102; 257/103;	
5	☐	☐	US 6233267 B1	20010515	12	Blue/ultraviolet/green vertical cavity surface emitting laser employing latera	372/46	372/45	

Hits   Details   HTML

Ready   NUM

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Active
- L1: (14) n-type adj bragg adj reflector
- L2: (175) n-type adj nitride
- L3: (5) 2 and bragg
- L4: (0) active adj region adj with$1 adj indium
- L5: (27053) active adj region
- L6: (1882) 5 and indium
- L7: (12035) quantum adj well
- L8: (2313) MQW
- L9: (12607) 7 8
- L10: (536) 9 and 6
- L11: (7) 10 and 2

Search   List   Browse   Queue   Clear

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10 and 2

BRS form   IS&R   Image   Text   HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☐	US 20020053676 A1	20020509	39	Nitride semiconductor device	257/88	
2	☑	☐	US 20020046693 A1	20020425	42	Nitride semiconductor growth method, nitride semiconductor substr	117/8	
3	☑	☐	US 20020008245 A1	20020124	8	SEMICONDUCTOR DEVICES WITH SELECTIVELY DOPED III-	257/87	
4	☑	☐	US 20010015442 A1	20010823	9	Semiconductor light emitting device having a silver p-contact	257/79	
5	☐	☐	US 6441393 B2	20020827	8	Semiconductor devices with selectively doped III-V nitride layers	257/13	257/79; 257/83;
6	☐	☐	US 6194743 B1	20010227	7	Nitride semiconductor light emitting device having a silver p-contact	257/94	257/745
7			US 6153010 A	20001128	35	Method of growing nitride	117/95	117/106;

Hits   Details   HTML
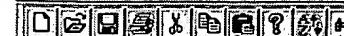
Ready   NUM

L4: (1443) 1 and nitride
L5: (455) 4 and (barrier adj layer)
L6: (127549) n adj type
L7: (127603) p adj type
L8: (96181) 6 and 7
L9: (330) 8 and 5
L10: (262) 9 and laser

Failed

Search   List   Browse   Queue   Clear

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9 and laser

BRS form   IS&R   Image   Text   HTML

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L1: (12029) quantum adj well
L2: (1181) quantum-well
L3: (12029) 1 or 2
L4: (1443) 1 and nitride
L5: (455) 4 and (barrier adj layer)
L6: (127549) n adj type
L7: (127603) p adj type
L8: (96181) 6 and 7

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9 and laser

BRS form IS&R Image Text HTML

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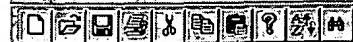
L10: (262) 9 and laser
L11: (12) 10 and (second adj barrier)
L12: (245) 10 and In
L13: (245) 12 and barrier
L14: (226) 13 and second
L15: (120) 14 and indium
Failed
(27) (((semiconductor and gate) and isotropic) and (n

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14 and indium

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Hits   Details   HTML

Ready   NUM

File View Edit Tools Window Help

L7: (127603) p adj type
L8: (96181) 6 and 7
L9: (330) 8 and 5
L10: (262) 9 and laser
L11: (12) 10 and (second adj barrier)
L12: (245) 10 and In
L13: (245) 12 and barrier

Failed

Search   List   Browse   Queue   Clear

DBs   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   ☐ Plurals

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12 and barrier

BRS form   IS&R...   Image   Text   HTML

U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R

Hits   Details   HTML

Ready   NUM